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# АПвЭАкП-15 1x150 ТУ У 31.3-00214534-017-2003

Single-core power cables with aluminium conductor, with XLPE, aluminium-wire armoured, with polyethylene outer sheath

For the cable of this mark correspond the foreign-made analogues:

AI/XLPE/CWS/PE/AWA/MDPE (GB) · XHAKXSAx (PL)

Due to non-magnetic armour, cables operate at AC

Technical cable requirements correspond to IEC 60502-2

### Cables are used for laying:

- in places, where small mechanical impacts on cable are possible, including tensile forces
- in soil (trenches)
- in the air, including cable structures, if provided the additional fire protection

It is possible to manufacture cables with extruded semiconductor layer along outer sheath.

Order entry example:

АПВЭАКП-П-15 1х150/25 ТУ У 31.3-00214534-017-2003

An extruded semiconductor layer along outer sheath ensures the correct testing of cable line with sections of underground laying in polymer pipes.

It is possible to manufacture cables with an integrated fiber-optic module.

Order entry example:

АПвЭАкП-15 1x150/25 (ОМ) ТУ У 31.3-00214534-017-2003

In conjunction with the DTS system, the integrated fiber-optic module can act as a distributed cable line temperature sensor.

It is possible to manufacture cable with

Order entry example:

АПвЭАкП-15 1х150/25 (ожк) ТУ У 31.3-00214534-017-2003

It is possible to manufacture cable with sealed conductor.

Order entry example:

АПВЭАКП-15 1х150/25 (г) ТУ У 31.3-00214534-017-2003







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## **TECHNICAL SPECIFICATIONS**

kV mm² mm mm² kA	15 17.5 1 x 150 4.5 25 5.1 14.2
mm² mm mm² kA kA	1 x 150 4.5 25 5.1 14.2
mm mm² kA kA	4.5 25 5.1 14.2
mm² kA kA	25 5.1 14.2
kA kA	<ul><li>5.1</li><li>14.2</li></ul>
kA A	14.2
A	
A	
	368
	368
Α	440
Α	281
Α	288
рС	6
°C	+90
°C	+130
°C	+250
°C	-60 +50
mm	672
mm	42
g/km	1890
m, t	# 18аУД-40: 903 • 2.2
	# 20аУД-60: 1026 • 2.6
	# 22УД-60: 1056 • 2.9
ĺ	A A pC C C C C C C C C Mmm mm g/km

#### Notes:

When ordering it is neccesary to agree the factory length of the product with the manufacturer

<sup>\*</sup> Long permissible current loads are calculated for the following conditions: conductor temperature 90 °C, air temperature 30 °C, soil temperature 20 °C, thermal resistivity of soil 1.5 °K • m/W, laying depth in the soil 0.8 m, while laying in flat formation the distance between cables in clear is equal to the cable diameter, while laying in trefoil formation cables are laid side by side, shields are earthed on both ends of the line

<sup>\*\*</sup> The external diameter may differ from the rated up to  $\pm$  10 %

<sup>\*\*\*</sup> Отклонение фактической массы брутто от указанного значения может составлять  $\pm\,7\,\%$ 



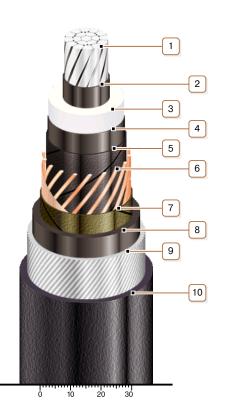




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#### **CONSTRUCTION**

- 1. Aluminium multiwire compacted conductor
- It is possible to manufacture cable with a single-wire conductor
- · It is possible to manufacture cable with sealed conductor.
- 2. Inner extruded semiconducting layer
- 3. XLPE insulation
- 4. Outer extruded semiconducting layer
- 5. Lapping layer of semiconductive swellable tape
- 6. Copper screen
- 7. Lapping layer of nonwoven cloth tape
- 8. Extruded bedding of polyethylene
- 9. Aluminium-wire armour
- 10. Outer sheath of polyethylene or polyethylene copolymer

Note: It is possible to manufacture cable with extruded semiconductor layer along outer sheath